



Atty.
Dkt. No.

M#

Client Ref.

308270

P-1812.000-US

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

Applicant: DIERICHS

Appl. No. 10/775,326

Filing Date: February 11, 2004

Date: July 2, 2004

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of

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Examiner: Unknown

Group Art Unit: ~~2042~~ 1756

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Brittany Raymond

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					Enclosed	No	Enclosed	No
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	PR EP 0023231	02/1981	EUROPE	TABARELLI et al.	X			
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	WR JP 62-121417	06/1987	JAPAN	NAKAZAWA	X			
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Examiner *Brittany Raymond*

Date Considered: 2/23/2007

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

FORM PTO-1449 (modified)
To: U.S. Department of Commerce
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English Abstract

Translation
Readily
Available

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						Enclosed	No	Enclosed	No
BR	LR	JP 07-220990	08/1995	JAPAN	FUKUDA <i>et al.</i>	X			
	MR	JP 10-228661	08/1998	JAPAN	KUROKAWA	X			
	NR	JP 10-255319	09/1998	JAPAN	SUENAGA <i>et al.</i>	X			
	OR	JP 10-303114	11/1998	JAPAN	SUWA	X		X	
	PR	JP 10-340846	12/1998	JAPAN	KUDO	X		X	
	QR	JP 2001-091849	04/2001	JAPAN	AIZAKI <i>et al.</i>	X			
	RR	JP 07-132262	05/1995	Japan	HIRAKAWA <i>et al.</i>	X			
	SR	JP 58-202448	11/1983	Japan	KAWAMURA <i>et al.</i>	X			
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BR	VR	WO 03/077036	09/2003	PCT	SCHUSTER	X			

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Examiner: Unknown

Group Art Unit: 2842 1756

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BR						
CR						

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						Enclosed	No	Enclosed	No
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BR	ER	DD 221 563	04/1985	GERMANY	PFORR et al.		X		
BR	FR	JP 11-176727	07/1999	JAPAN	SHIRAISHI	X			
	GR								

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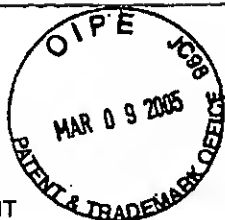
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Date Considered: 2/23/2007

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INFORMATION DISCLOSURE STATEMENT
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Applicant: MARCEL MTM DIERICHs

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<i>↓</i>	CR 2003/0174408	09/2003	ROSTALSKI et al.	359	642	
<i>↓</i>	DR 2004/0119954	06/2004	KAWASHIMA et al.	355	30	
<i>BR</i>	ER 2004/0125351	07/2004	KRAUTSCHIK	355	53	
	FR					
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<i>↓</i>	IR JP 2004-193252	07/2004	Japan	Not Available	X			
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<i>↓</i>	KR WO 2004/053951 A1	06/2004	PCT	MAGOME et al.	X			
<i>↓</i>	LR WO 2004/053952 A1	06/2004	PCT	MAGOME et al.	X			
<i>↓</i>	MR WO 2004/053953 A1	06/2004	PCT	NEI et al.	X			
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<i>↓</i>	TR WO 2004/053596 A2	06/2004	PCT	GRAUPNER	X			
<i>↓</i>	UR WO 2004/055803 A1	07/2004	PCT	VAN SANTEN	X			
<i>↓</i>	VR WO 2004/057589 A1	07/2004	PCT	NEIJZEN et al.	X			
<i>BR</i>	WR WO 2004/057590 A1	07/2004	PCT	VAN SANTEN et al.	X		X	
	XR							
	YR							

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